

Vishay Siliconix

N-Channel 150-V (D-S) MOSFET

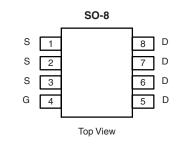
PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
150	0.050 at V _{GS} = 10 V	5.0		

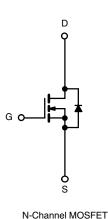
FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC



HALOGEN FREE Available





Ordering Information: Si4488DY-T1-E3 (Lead (Pb)-free) Si4488DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise ı	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	150		V
Gate-Source Voltage		V _{GS}	± 20		V
	T _A = 25 °C	- I _D	5.0	3.5	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		4.0	2.8	
Pulsed Drain Current		I _{DM}	50		А
Avalanche Current	L = 0.1 mH	I _{AS}	25		
Continuous Source Current (Diode Conduction) ^a		۱ _S	2.8	1.4	
	T _A = 25 °C	P _D	3.1	1.56	w
Maximum Power Dissipation ^a	T _A = 70 °C	۲D	2.0	1.0	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55	to 150	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum hunsting to Anthing 18	t ≤ 10 s	R _{thJA}	33	40		
Maximum Junction-to-Ambient ^a	Steady State		65	80	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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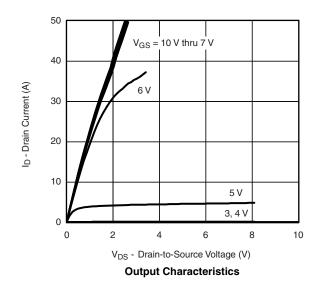
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.0			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA		
		V _{DS} = 120 V, V _{GS} = 0 V			1			
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 120 V, V_{GS} = 0 V, T_{J} = 55 °C			5	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			А		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 5 \text{ A}$		0.041	0.050	Ω		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 5 \text{ A}$		18		S		
Diode Forward Voltage ^a	V _{SD}	$I_{S} = 2.8 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.1	V		
Dynamic ^b	•		•					
Total Gate Charge	Qg			30	36			
Gate-Source Charge	Q _{gs}	V_{DS} = 75 V, V_{GS} = 10 V, I_{D} = 5 A		8.5		nC		
Gate-Drain Charge	Q _{gd}			8.5				
Gate Resistance	R _g		0.2	0.85	1.2	Ω		
Turn-On Delay Time	t _{d(on)}			12	18			
Rise Time	t _r	V_{DD} = 75 V, R_L = 15 Ω		7	11			
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D} \cong$ 5 A, V_GEN = 10 V, R_g = 6 Ω		22	33	ns		
Fall Time	t _f			10	15			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.8 A, dl/dt = 100 A/μs		40	70			

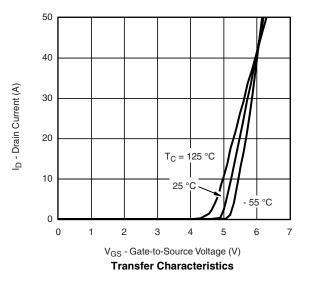
Notes:

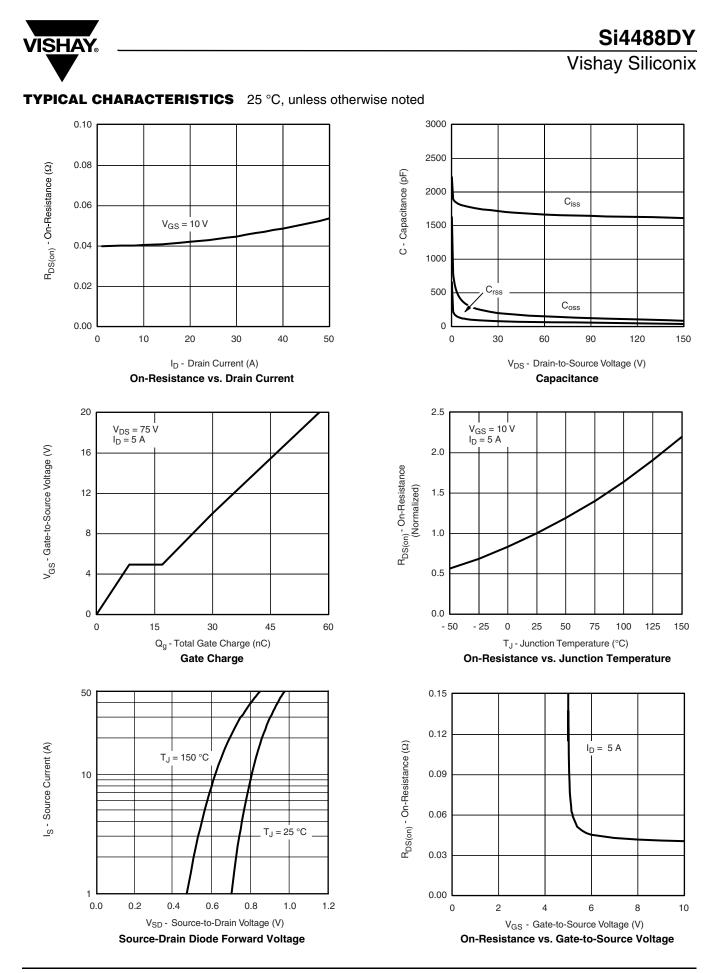
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





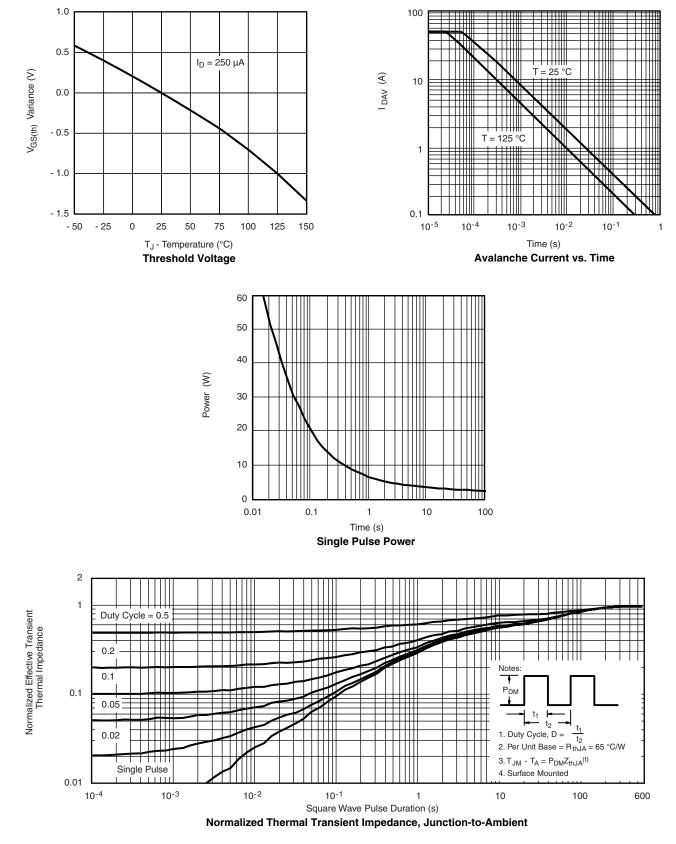


Document Number: 71240 S09-0705-Rev. C, 27-Apr-09

Si4488DY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

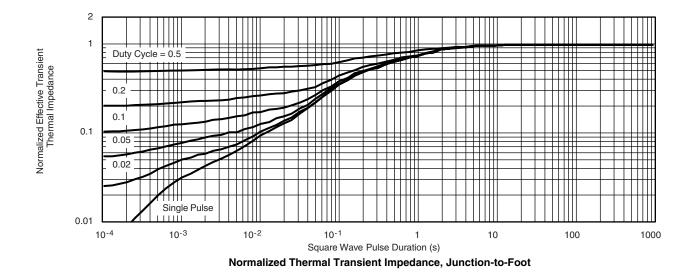


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Si4488DY Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71240.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INC	HES		
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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